

Supporting Information

Thermally stable Indium based metal–organic frameworks with high dielectric permittivity

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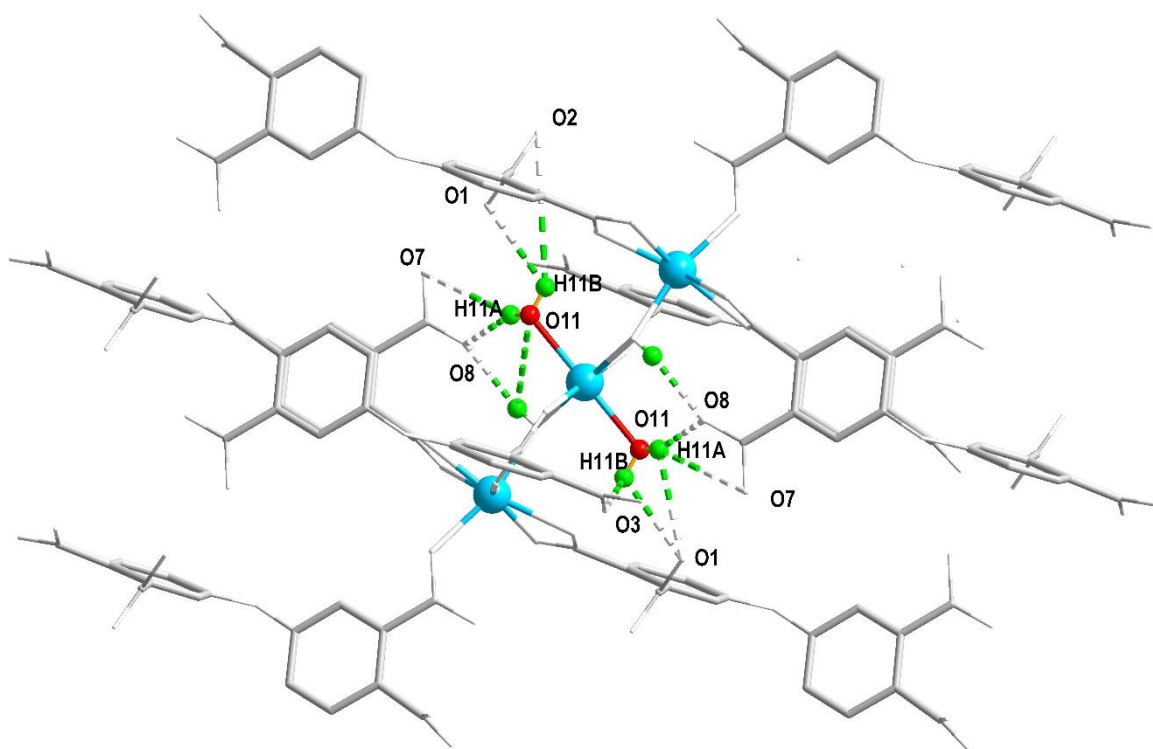


Fig. S1 Hydrogen bonding interactions of comound 1 ($\text{O8-H11A}\cdots\text{O11} = 1.89 \text{ \AA}$; $\text{O2-H11B}\cdots\text{O11} = 3.90 \text{ \AA}$; $\text{O8-H11B}\cdots\text{O11} = 2.69 \text{ \AA}$; $\text{O8-H10A}\cdots\text{O10} = 2.10 \text{ \AA}$; $\text{O11-H10A}\cdots\text{O10} = 2.90 \text{ \AA}$; $\text{O7-H11A}\cdots\text{O11} = 3.20 \text{ \AA}$; $\text{O7-H11}\cdots\text{BO11} = 3.05 \text{ \AA}$; $\text{O1-H11A}\cdots\text{O11} = 2.83 \text{ \AA}$; $\text{O1-H11B}\cdots\text{O11} = 2.66 \text{ \AA}$).

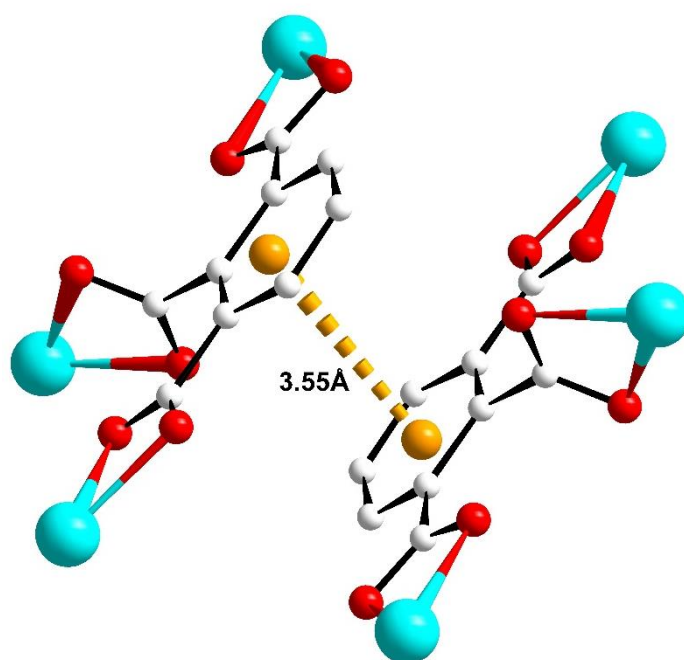


Fig. S2 The weak parallel-displaced $\pi\cdots\pi$ stacking interactions in between the neighboring btc ligands in compound 2.

Dielectric relaxation

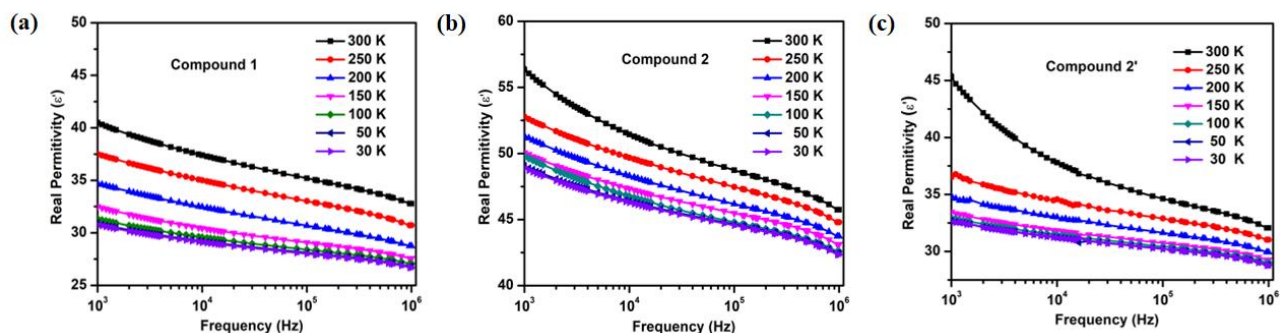


Fig. S3 Frequency dependent permittivity (ϵ') of compound 1 (a), compound 2 (b), and compound 2' (c) at different temperatures.

Dielectric loss versus frequency

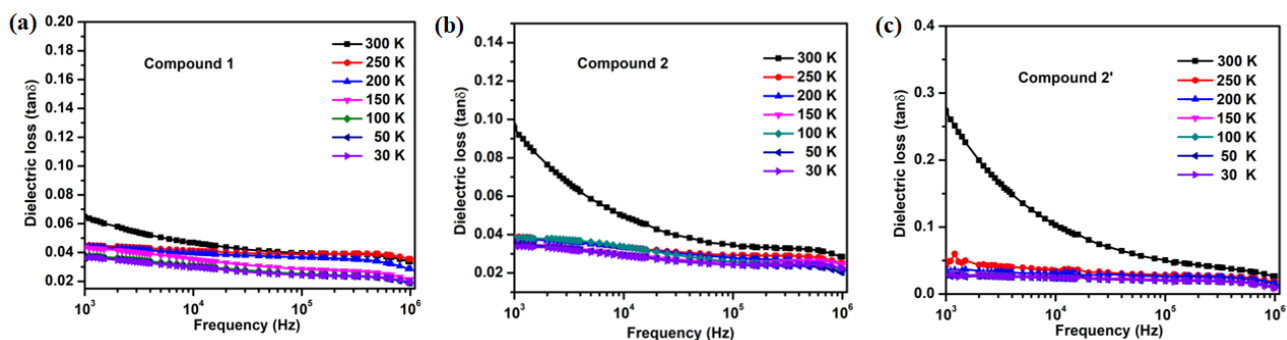


Fig. S4 Frequency dependent dielectric loss ($\tan\delta$) of compound 1 (a), compound 2 (b), and compound 2' (c) at different temperatures.

Electrical conductivity versus temperature

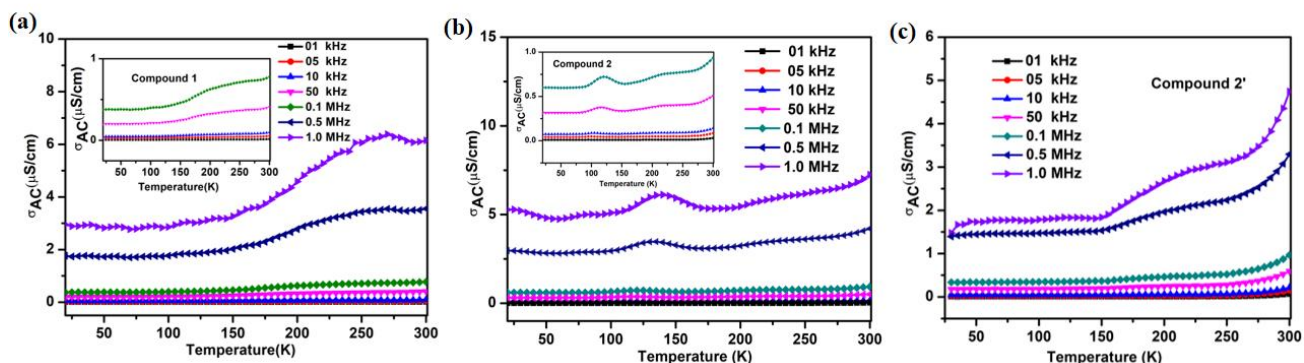


Fig. S5 temperature dependent electrical conductivities of compound 1 (a), compound 2 (b), and compound 2' (c) at different frequencies.

Electrical conductivity versus frequency

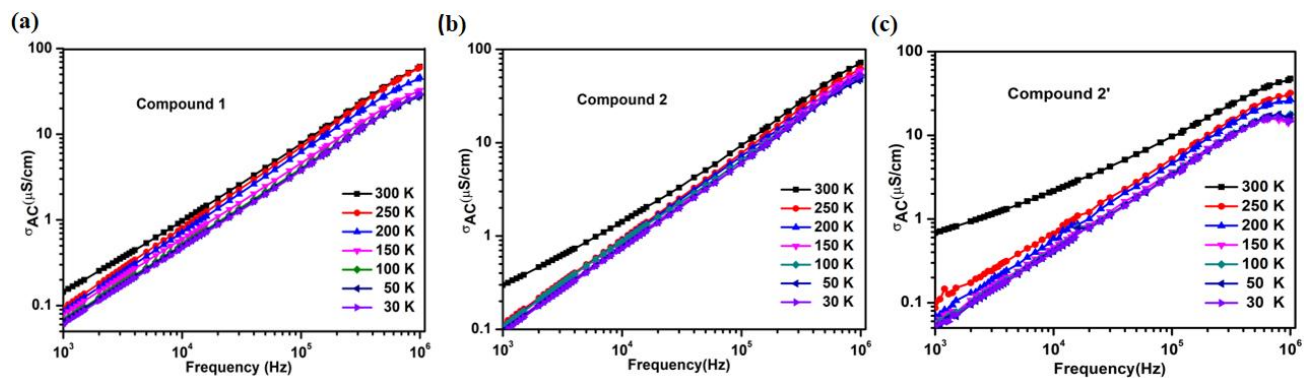


Fig. S6 Frequency dependent electrical conductivities of compound 1 (a), compound 2 (b), and compound 2' (c) at different temperatures.

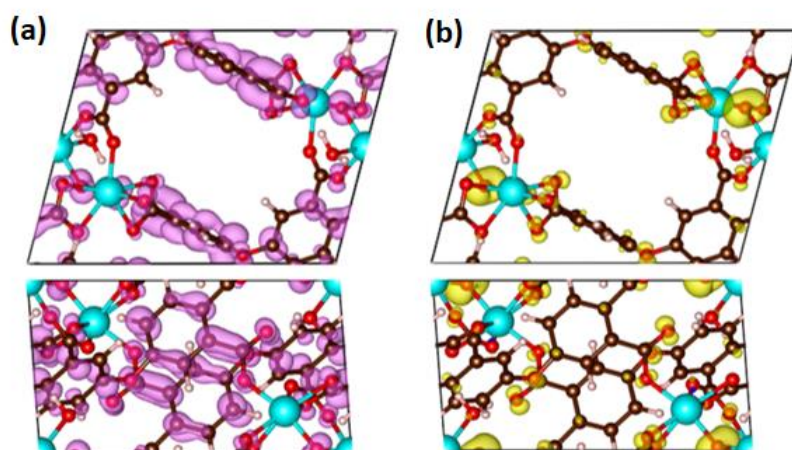


Fig. S7 The side (top panel) and top (bottom panel) views of orbital feature for the (a) CBM and (b) VBM of compound 1

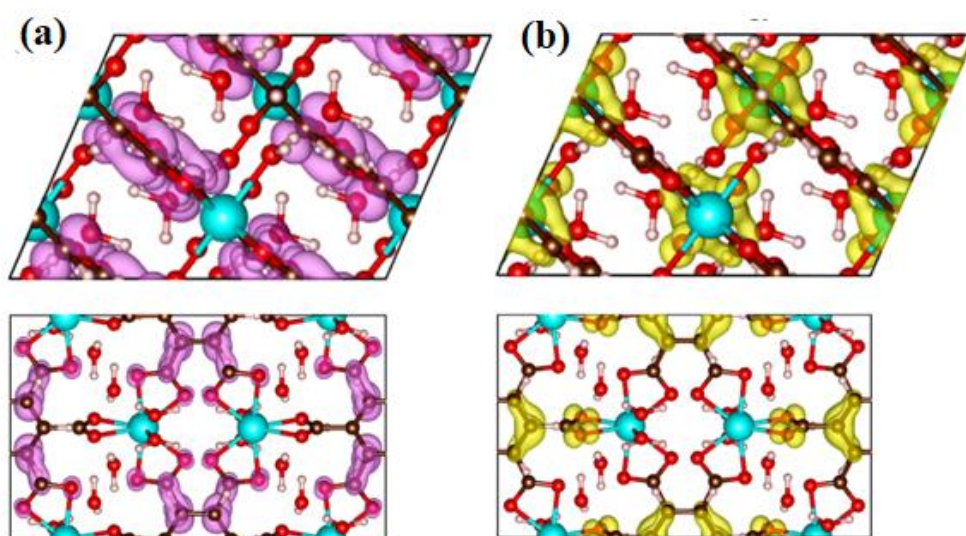


Fig. S8 The side (top panel) and top (bottom panel) views of orbital feature for the (a) CBM and (b) VBM of compound 2

Crystal Data of Compound 1 (CCDC 1996451)

Table 1. Crystal data and structure refinement for compound **1**

Empirical formula	C ₃₂ H ₂₆ In ₃ Na O ₂₆
Formula weight	1193.98
Temperature	200(2) K
Wavelength	0.71073 Å
Crystal system	Triclinic
Space group	$P\bar{1}$
Unit cell dimensions	$a = 7.4109(4)$ Å $b = 10.7283(8)$ Å $c = 13.1626(7)$ Å $\beta = 90.383(2)^\circ$
Volume	981.17(10) Å ³
Z	1
Density (calculated)	2.021 Mg/m ³
Absorption coefficient	1.859 mm ⁻¹
$F(000)$	584
Crystal size	0.22 x 0.03 x 0.02 mm ³
Theta range for data collection	2.84 to 25.05°
Index ranges	-8 ≤ h ≤ 8, -12 ≤ k ≤ 12, -15 ≤ l ≤ 15
Reflections collected	18965
Independent reflections	3446 [$R(\text{int}) = 0.0569$]
Completeness to $\theta = 25.05^\circ$	99.6 %
Absorption correction	Semi-empirical from equivalents
Max. and min. transmission	0.7452 and 0.5995
Refinement method	Full-matrix least-squares on F^2
Data / restraints / parameters	3455 / 7 / 288
Goodness-of-fit on F^2	1.049
Final R indices [$I > 2\sigma(I)$]	$R_1 = 0.0331$, $wR_2 = 0.0793$
R indices (all data)	$R_1 = 0.0409$, $wR_2 = 0.0846$
Largest diff. peak and hole	1.502 and -0.861 e.Å ⁻³
^a $R_1 = \sum F_o - F_c / \sum F_o $; $wR_2 = [\sum w(F_o^2 - F_c^2)_2 / \sum w(F_o^2)_2]^{1/2}$	

Crystal Data of Compound 2 (CCDC 1996452)**Table 2.** Crystal data and structure refinement for compound 2

Empirical formula	C ₉ H ₁₁ In O ₁₀
Formula weight	394.00
Temperature	200(2) K
Wavelength	0.71073 Å
Crystal system	Monoclinic
Space group	<i>C</i> 2/ <i>c</i>
Unit cell dimensions	<i>a</i> = 10.3577(5) Å <i>b</i> = 15.9403(8) Å <i>c</i> = 7.2865(3) Å <i>β</i> = 113.346(1)°
Volume	1104.54(9) Å ³
<i>Z</i>	4
Density (calculated)	2.369 Mg/m ³
Absorption coefficient	2.197 mm ⁻¹
<i>F</i> (000)	776
Crystal size	0.25 x 0.21 x 0.11 mm ³
Theta range for data collection	2.49 to 25.05°
Index ranges	-12 ≤ <i>h</i> ≤ 12, -18 ≤ <i>k</i> ≤ 18, -8 ≤ <i>l</i> ≤ 8
Reflections collected	9865
Independent reflections	969 [<i>R</i> (int) = 0.0332]
Completeness to theta = 25.05°	98.3%
Absorption correction	multi-scan
Max. and min. transmission	0.7942 and 0.6097
Refinement method	Full-matrix least-squares on <i>F</i> ²
Data / restraints / parameters	969 / 0 / 93
Goodness-of-fit on <i>F</i> ²	1.029
Final <i>R</i> indices [<i>I</i> > 2σ(<i>I</i>)]	<i>R</i> 1 = 0.0113, <i>wR</i> 2 = 0.0284
<i>R</i> indices (all data)	<i>R</i> 1 = 0.0115, <i>wR</i> 2 = 0.0285
Largest diff. peak and hole	0.275 and -0.345 e.Å ⁻³

$$^a R_1 = \sum ||F_o| - |F_c|| / \sum |F_o|; wR_2 = [\sum w(F_o^2 - F_c^2)_2 / \sum w(F_o^2)_2]^{1/2}$$